

EGFM101-S THRU EGFM105-S

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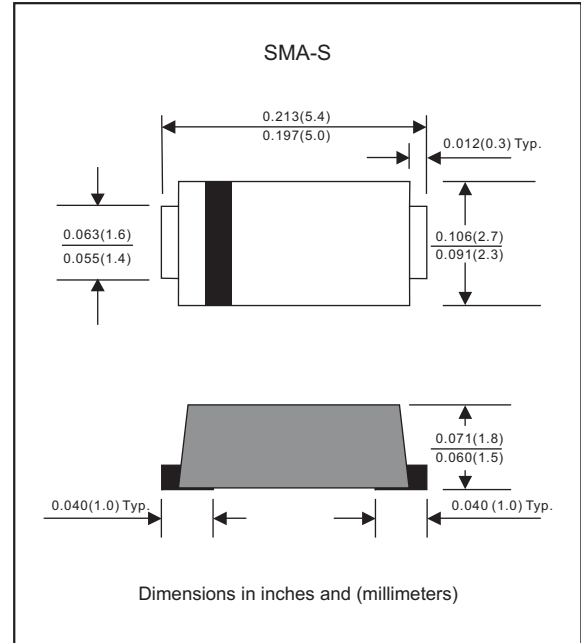
EGFM101-S THRU EGFM105-S

1.0A Surface Mount Efficient Fast Rectifiers- 50-600V

Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- High current & surge capability.
- Low forward drop voltage
- Glass passivated chip junction.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228
- Suffix "-H" indicates Halogen free parts, ex. EGFM101-S-H.

Package outline



Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, DO-214AC / SMA-S
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.05 gram

Maximum ratings and Electrical Characteristics (AT T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.2	I _o			1.0	A
Forward surge current	8.3ms single half sine-wave\ (JEDEC methode)	I _{FSM}			30	A
Reverse current	V _R = V _{RRM} T _J = 25°C	I _R			5.0	μA
	V _R = V _{RRM} T _J = 125°C				100	
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	C _J		15		pF
Storage temperature		T _{STG}	-65		+175	°C

SYMBOLS	V _{RRM} ^{*1} (V)	V _{RMS} ^{*2} (V)	V _R ^{*3} (V)	V _F ^{*4} (V)	t _{rr} ^{*5} (ns)	Operating temperature T _J , (°C)
EGFM101-S	50	35	50	0.875	25	-55 to +150
EGFM102-S	100	70	100			
EGFM103-S	200	140	200			
EGFM104-S	400	280	400	1.25		
EGFM105-S	600	420	600	1.75		

- *1 Repetitive peak reverse voltage
- *2 RMS voltage
- *3 Continuous reverse voltage
- *4 Maximum forward voltage@I_F=1.0A
- *5 Maximum Reverse recovery time, note 1

Note 1. Reverse recovery time test condition, I_F=0.5A, I_R=1.0A, I_{RR}=0.25A

Rating and characteristic curves (EGFM101-S THRU EGFM105-S)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

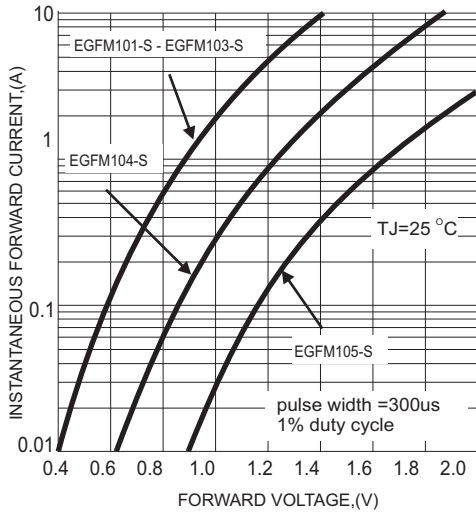


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

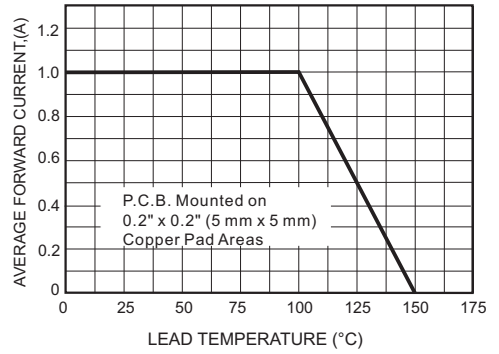
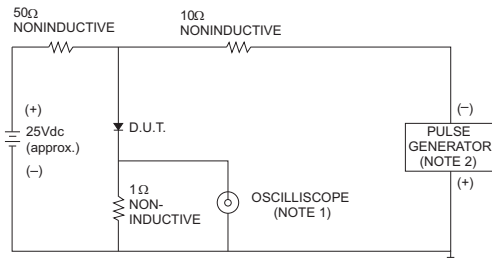


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time = 7ns max., Input Impedance = 1 megohm, 22pF.
2. Rise Time = 10ns max., Source Impedance = 50 ohms.

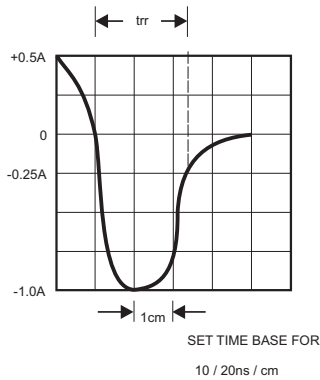


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

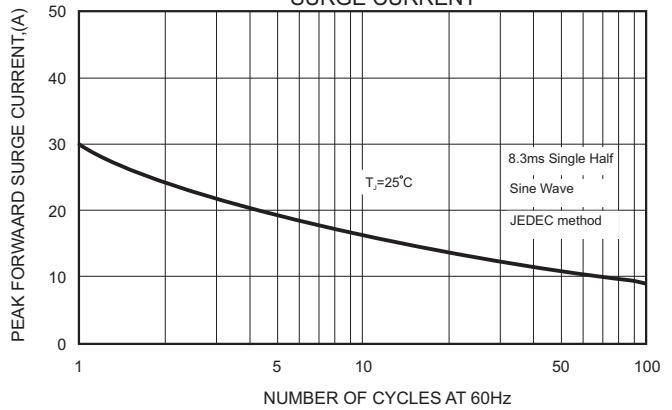
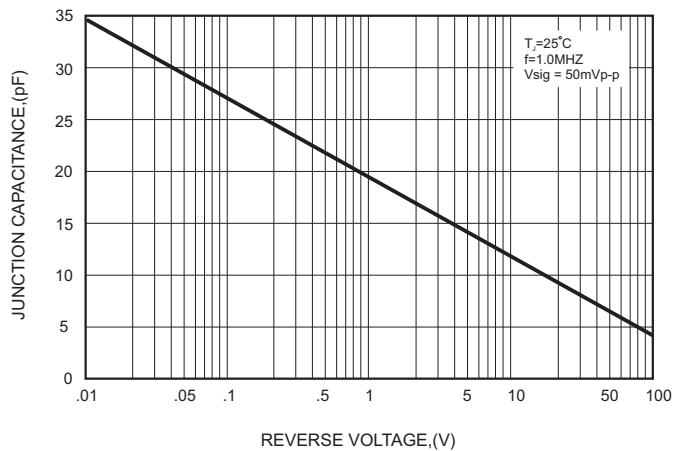




FIG.5-TYPICAL JUNCTION CAPACITANCE



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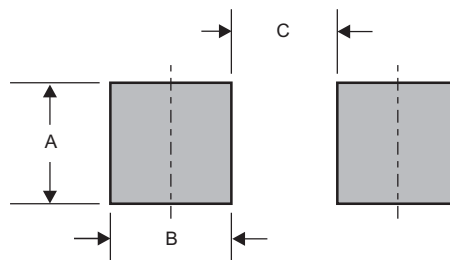
Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Marking

Type number	Marking code
EGFM101-S	E11
EGFM102-S	E12
EGFM103-S	E13
EGFM104-S	E14
EGFM105-S	E15

Suggested solder pad layout

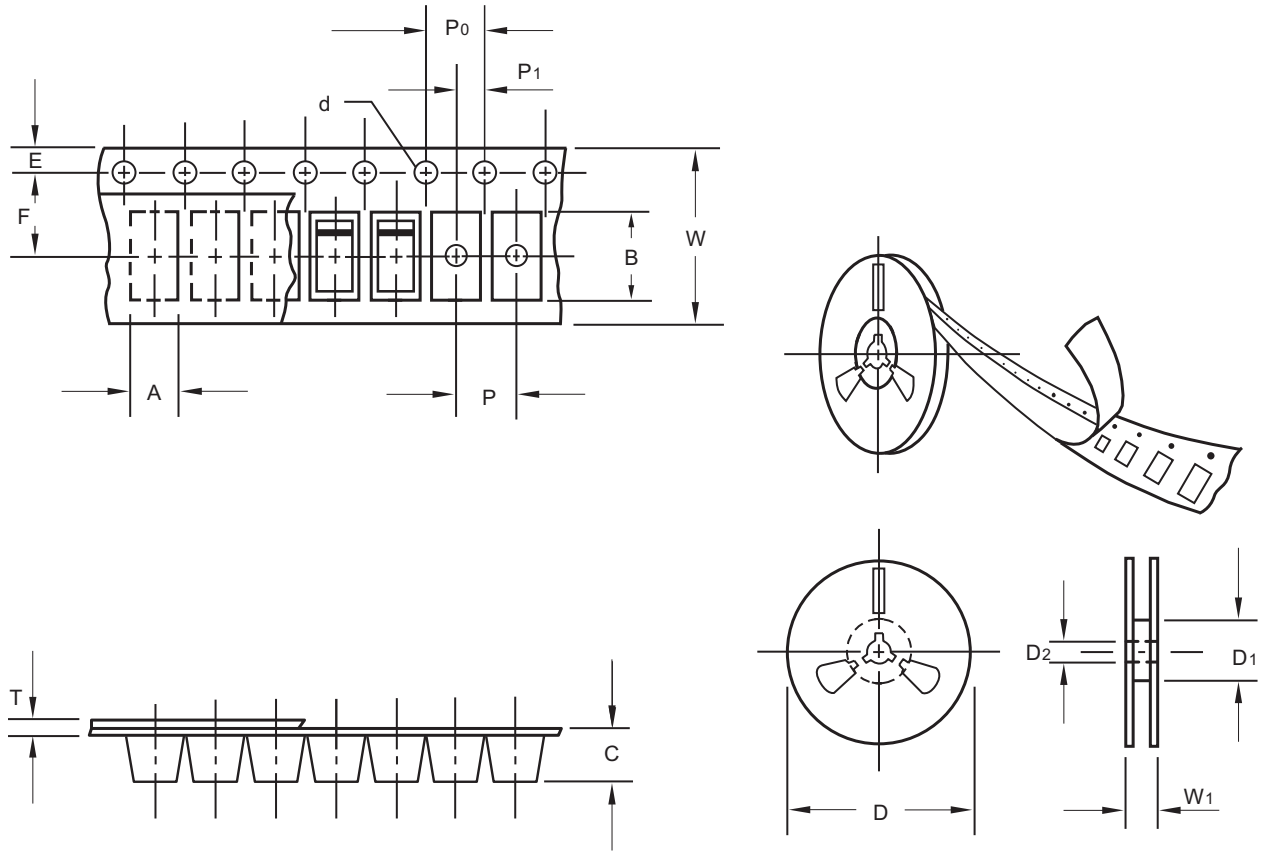


Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SMA-S	0.063 (1.60)	0.059 (1.50)	0.110 (2.80)

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Packing information



unit:mm

Item	Symbol	Tolerance	SMA-S
Carrier width	A	0.1	2.90
Carrier length	B	0.1	5.50
Carrier depth	C	0.1	2.10
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	330.00
13" Reel inner diameter	D ₁	min	50.00
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D ₁	min	62.00
Feed hole diameter	D ₂	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	5.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P ₀	0.1	4.00
Embossment center	P ₁	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	12.00
Reel width	W ₁	1.0	18.00

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at $260\pm 5^{\circ}\text{C}$ for $10\pm 2\text{sec}$. immerse body into solder $1/16''\pm 1/32''$	MIL-STD-750D METHOD-2031
2. Solderability	at $245\pm 5^{\circ}\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=150^{\circ}\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^{\circ}\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^{\circ}\text{C}$, $I_F = I_o$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A=121^{\circ}\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to $+125^{\circ}\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	8.3ms single half sine-wave , one surge.	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^{\circ}\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031